

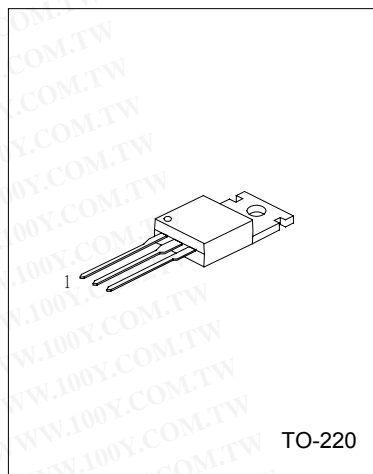
## NPN EPITAXIAL TRANSISTOR

## DESCRIPTION

The UTC 2SD880 is designed for audio frequency power amplifier applications.

## FEATURE

- \*High DC Current Gain:  
hFE=300(Max.)(VCE=5V, IC=0.5A)
- \*Low Saturation Voltage:  
VCE(sat)=1.0V(Max.)(IC=3A, IB=0.3A)
- \*High Power Dissipation:  
PC=30W (Ta=25°C)
- \*Complementary to 2SB834



TO-220

1:BASE 2:COLLECTOR 3:EMITTER

\*Pb-free plating product number: 2SD880L

## ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Maximum Voltages and currents			
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCEO	60	V
Emitter to Base Voltage	VEBO	7	V
Collector Current	IC	3	A
Base Current	IB	0.5	A
Maximum Power Dissipation			
Total Power Dissipation	PD	30	W
Maximum Temperature			
Junction Temperature Range	T <sub>OPR</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ +150	°C

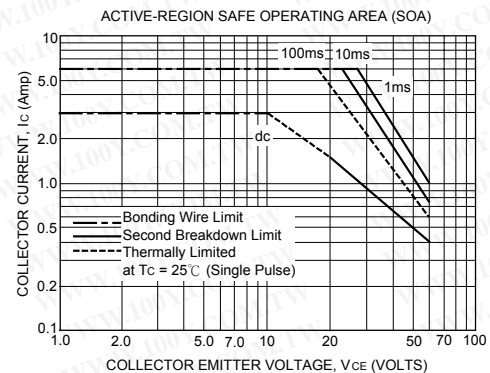
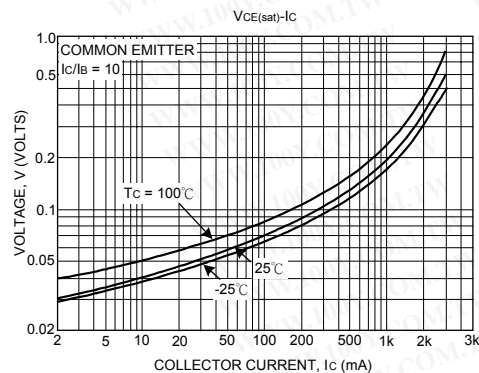
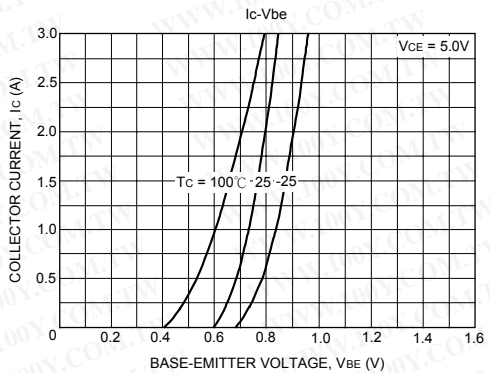
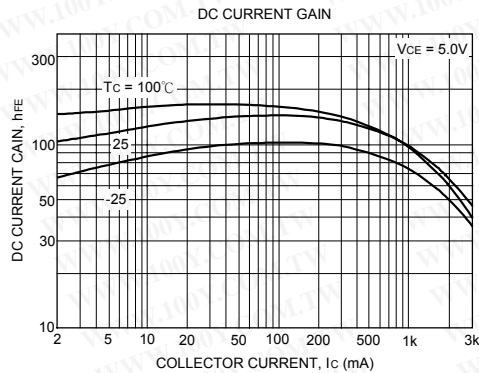
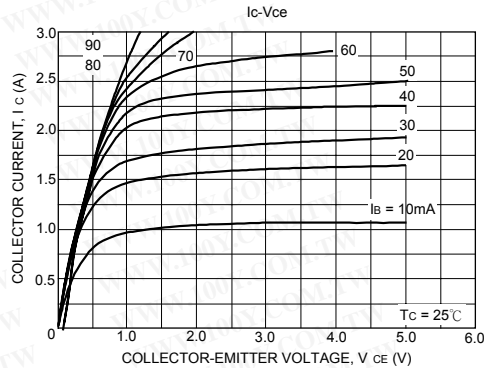
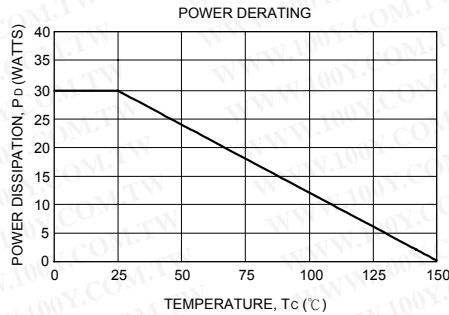
## ELECTRICAL CHARACTERISTICS(Ta=25°C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	BVCEO	IC=50mA, IE=0	60			V
Collector Cut-Off Current	ICBO	V <sub>CB</sub> =60V, IE=0			100	μA
Emitter Cut-Off Current	IEBO	V <sub>EB</sub> =7V, IC=0			100	μA
Collector-Emitter Saturation Voltage	VCE(SAT)	IC=3A, IB=300mA			1	V
Base-Emitter Saturation Voltage	VBE(ON)	VCE=5V, IC=500mA			1	V
DC Current Gain	hFE	IC=500mA, VCE=5V	60		300	
Current gain bandwidth product	f <sub>T</sub>	VCE=5V, IC=500mA		3		MHZ

**CLASSIFICATION of hFE**

RANK	O	Y	GR
RANGE	60-120	100-200	150-300

**TYPICAL CHARACTERISTICS**



勝特力材料 886-3-5753170  
 勝特力电子(上海) 86-21-34970699  
 勝特力电子(深圳) 86-755-83298787  
 Http://www.100y.com.tw